

STARPOWER

SEMICONDUCTOR

IGBT

GD75TPT120C6S

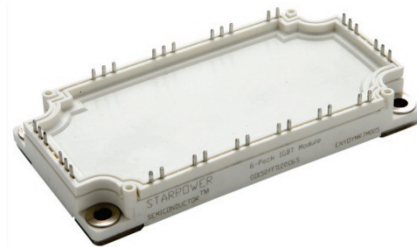
1200V/75A 12 in one-package

General Description

STARPOWER IGBT Power Module provides ultra low conduction loss as well as short circuit ruggedness. They are designed for the applications such as general inverters and UPS.

Features

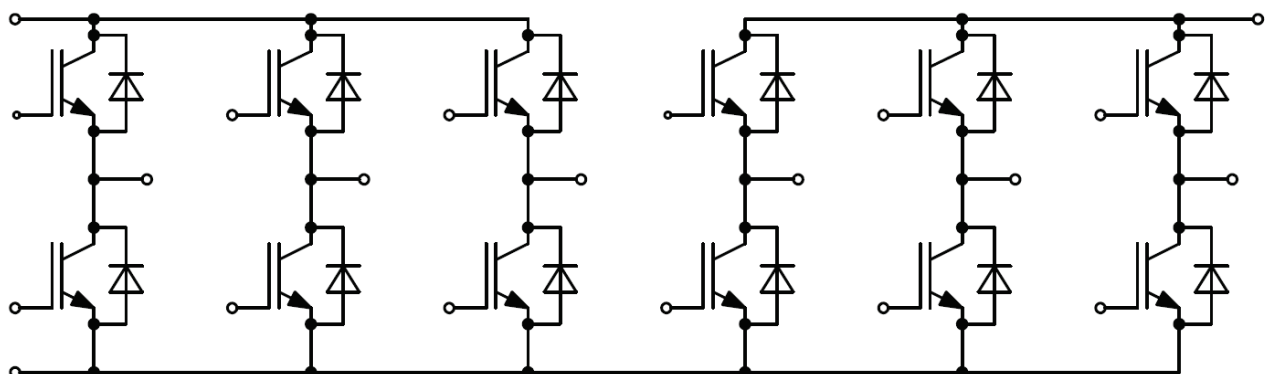
- Low $V_{CE(sat)}$ Trench IGBT technology
- 10 μ s short circuit capability
- $V_{CE(sat)}$ with positive temperature coefficient
- Maximum junction temperature 175 °C
- Low inductance case
- Fast & soft reverse recovery anti-parallel FWD
- Isolated copper baseplate using DBC technology



Typical Applications

- Inverter for motor drive
- AC and DC servo drive amplifier
- Uninterruptible power supply

Equivalent Circuit Schematic



Absolute Maximum Ratings $T_C=25^{\circ}\text{C}$ unless otherwise noted**IGBT**

Symbol	Description	Values	Unit
V_{CES}	Collector-Emitter Voltage	1200	V
V_{GES}	Gate-Emitter Voltage	± 20	V
I_C	Collector Current @ $T_C=25^{\circ}\text{C}$	110	A
	@ $T_C=95^{\circ}\text{C}$	75	A
I_{CM}	Pulsed Collector Current $t_p=1\text{ms}$	150	A
P_D	Maximum Power Dissipation @ $T_j=175^{\circ}\text{C}$	386	W

Diode

Symbol	Description	Values	Unit
V_{RRM}	Repetitive Peak Reverse Voltage	1200	V
I_F	Diode Continuous Forward Current	75	A
I_{FM}	Diode Maximum Forward Current $t_p=1\text{ms}$	150	A

Module

Symbol	Description	Values	Unit
T_{jmax}	Maximum Junction Temperature	175	$^{\circ}\text{C}$
T_{jop}	Operating Junction Temperature	-40 to +150	$^{\circ}\text{C}$
T_{STG}	Storage Temperature Range	-40 to +125	$^{\circ}\text{C}$
V_{ISO}	Isolation Voltage RMS, $f=50\text{Hz}$, $t=1\text{min}$	4000	V

IGBT Characteristics $T_c=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{CE(sat)}$	Collector to Emitter Saturation Voltage	$I_C=75\text{A}, V_{GE}=15\text{V}, T_j=25^\circ\text{C}$		1.85	2.30	V
		$I_C=75\text{A}, V_{GE}=15\text{V}, T_j=125^\circ\text{C}$		2.15		
		$I_C=75\text{A}, V_{GE}=15\text{V}, T_j=150^\circ\text{C}$		2.25		
$V_{GE(th)}$	Gate-Emitter Threshold Voltage	$I_C=2.6\text{mA}, V_{CE}=V_{GE}, T_j=25^\circ\text{C}$	5.3	5.8	6.3	V
I_{CES}	Collector Cut-Off Current	$V_{CE}=V_{CES}, V_{GE}=0\text{V}, T_j=25^\circ\text{C}$			1.0	mA
I_{GES}	Gate-Emitter Leakage Current	$V_{GE}=V_{GES}, V_{CE}=0\text{V}, T_j=25^\circ\text{C}$			100	nA
R_{Gint}	Internal Gate Resistance			10		Ω
C_{ies}	Input Capacitance	$V_{CE}=25\text{V}, f=1\text{MHz}, V_{GE}=0\text{V}$		4.30		nF
C_{res}	Reverse Transfer Capacitance				0.16	
Q_G	Gate Charge	$V_{GE}=-15 \dots +15\text{V}$		0.57		μC
$t_{d(on)}$	Turn-On Delay Time	$V_{CC}=600\text{V}, I_C=75\text{A}, R_G=2.2\Omega, V_{GE}=\pm 15\text{V}, T_j=25^\circ\text{C}$		160		ns
t_r	Rise Time			31		ns
$t_{d(off)}$	Turn-Off Delay Time			338		ns
t_f	Fall Time			78		ns
E_{on}	Turn-On Switching Loss			3.42		mJ
E_{off}	Turn-Off Switching Loss			4.18		mJ
$t_{d(on)}$	Turn-On Delay Time	$V_{CC}=600\text{V}, I_C=75\text{A}, R_G=2.2\Omega, V_{GE}=\pm 15\text{V}, T_j=125^\circ\text{C}$		168		ns
t_r	Rise Time			41		ns
$t_{d(off)}$	Turn-Off Delay Time			432		ns
t_f	Fall Time			150		ns
E_{on}	Turn-On Switching Loss			7.30		mJ
E_{off}	Turn-Off Switching Loss			6.41		mJ
$t_{d(on)}$	Turn-On Delay Time	$V_{CC}=600\text{V}, I_C=75\text{A}, R_G=2.2\Omega, V_{GE}=\pm 15\text{V}, T_j=150^\circ\text{C}$		170		ns
t_r	Rise Time			42		ns
$t_{d(off)}$	Turn-Off Delay Time			450		ns
t_f	Fall Time			168		ns
E_{on}	Turn-On Switching Loss			8.48		mJ
E_{off}	Turn-Off Switching Loss			7.22		mJ
I_{SC}	SC Data	$t_p \leq 10\mu\text{s}, V_{GE}=15\text{V}, T_j=150^\circ\text{C}, V_{CC}=900\text{V}, V_{CEM} \leq 1200\text{V}$		270		A

Diode Characteristics $T_c=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V_F	Diode Forward Voltage	$I_F=75\text{A}, V_{GE}=0\text{V}, T_j=25^\circ\text{C}$		1.70	2.15	V
		$I_F=75\text{A}, V_{GE}=0\text{V}, T_j=125^\circ\text{C}$		1.65		
		$I_F=75\text{A}, V_{GE}=0\text{V}, T_j=150^\circ\text{C}$		1.65		
Q_r	Recovered Charge	$V_R=600\text{V}, I_F=75\text{A},$ $-di/dt=1900\text{A}/\mu\text{s}, V_{GE}=-15\text{V}$ $T_j=25^\circ\text{C}$		7.28		μC
I_{RM}	Peak Reverse Recovery Current			87		A
E_{rec}	Reverse Recovery Energy			2.58		mJ
Q_r	Recovered Charge	$V_R=600\text{V}, I_F=75\text{A},$ $-di/dt=1900\text{A}/\mu\text{s}, V_{GE}=-15\text{V}$ $T_j=125^\circ\text{C}$		13.1		μC
I_{RM}	Peak Reverse Recovery Current			89		A
E_{rec}	Reverse Recovery Energy			4.50		mJ
Q_r	Recovered Charge	$V_R=600\text{V}, I_F=75\text{A},$ $-di/dt=1900\text{A}/\mu\text{s}, V_{GE}=-15\text{V}$ $T_j=150^\circ\text{C}$		14.5		μC
I_{RM}	Peak Reverse Recovery Current			90		A
E_{rec}	Reverse Recovery Energy			5.52		mJ

Module Characteristics $T_c=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Min.	Typ.	Max.	Unit
L_{CE}	Stray Inductance		20		nH
$R_{CC'+EE'}$	Module Lead Resistance, Terminal to Chip		2.50		m Ω
$R_{\theta JC}$	Junction-to-Case (per IGBT)			0.389	K/W
	Junction-to-Case (per Diode)			0.618	
$R_{\theta CS}$	Case-to-Sink (per IGBT)		0.176		K/W
	Case-to-Sink (per Diode)		0.280		
$R_{\theta CS}$	Case-to-Sink		0.009		K/W
M	Mounting Torque, Screw M5	3.0		6.0	N.m
G	Weight of Module		300		g

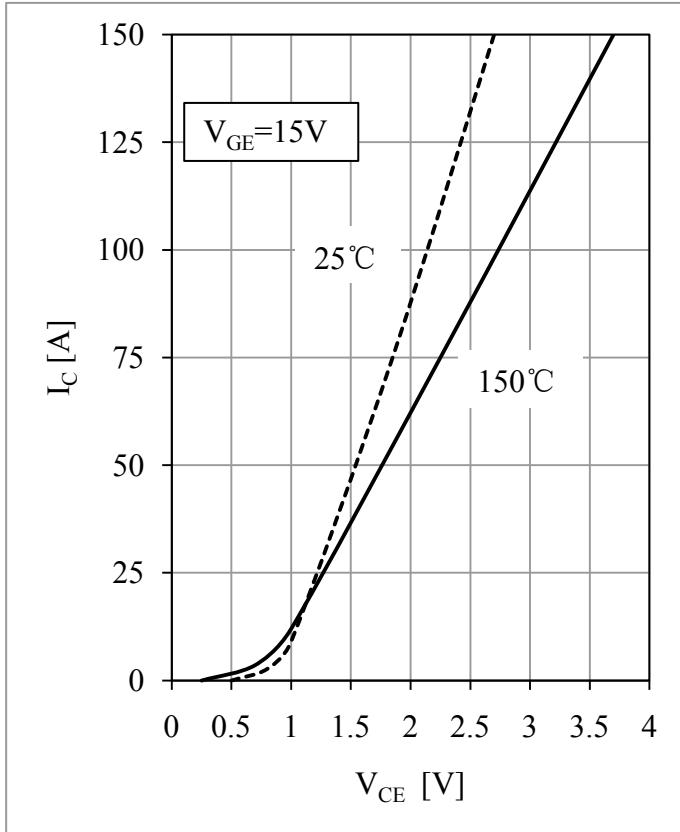


Fig 1. IGBT Output Characteristics

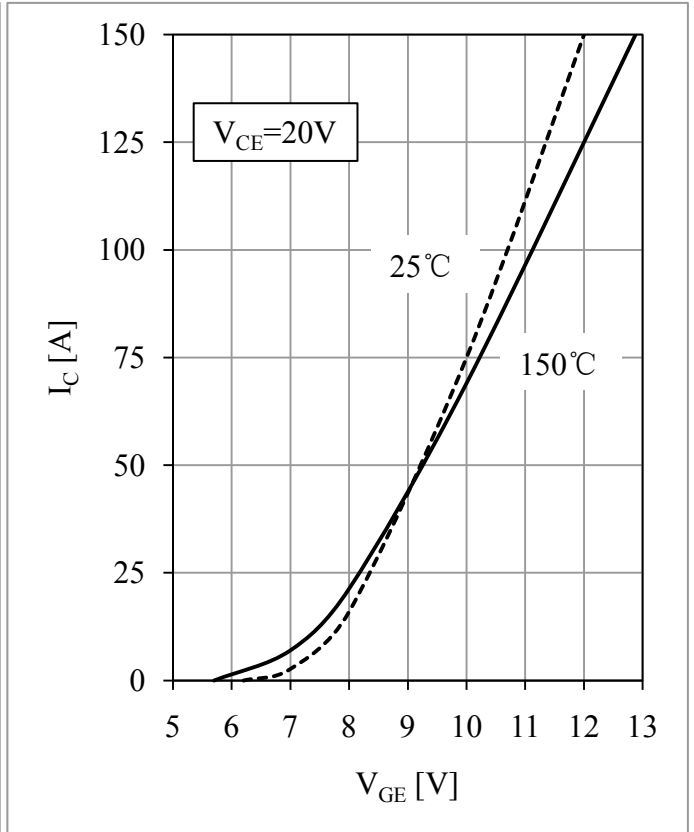


Fig 2. IGBT Transfer Characteristics

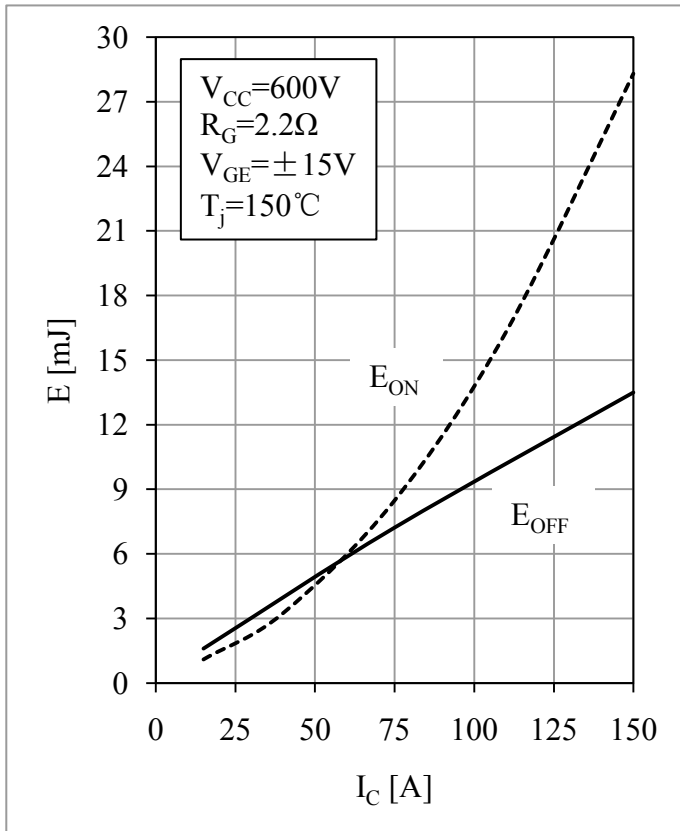


Fig 3. IGBT Switching Loss vs. I_C

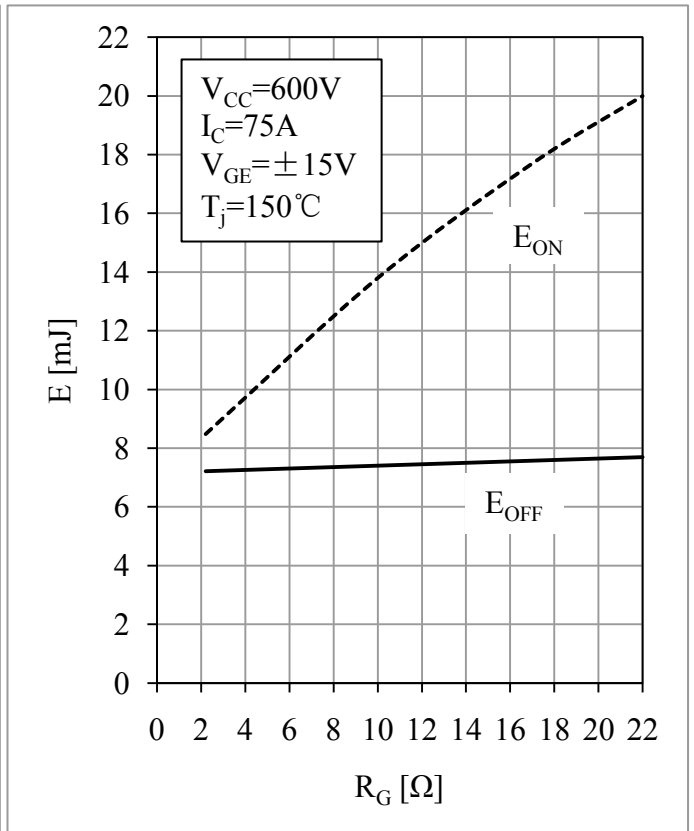


Fig 4. IGBT Switching Loss vs. R_G

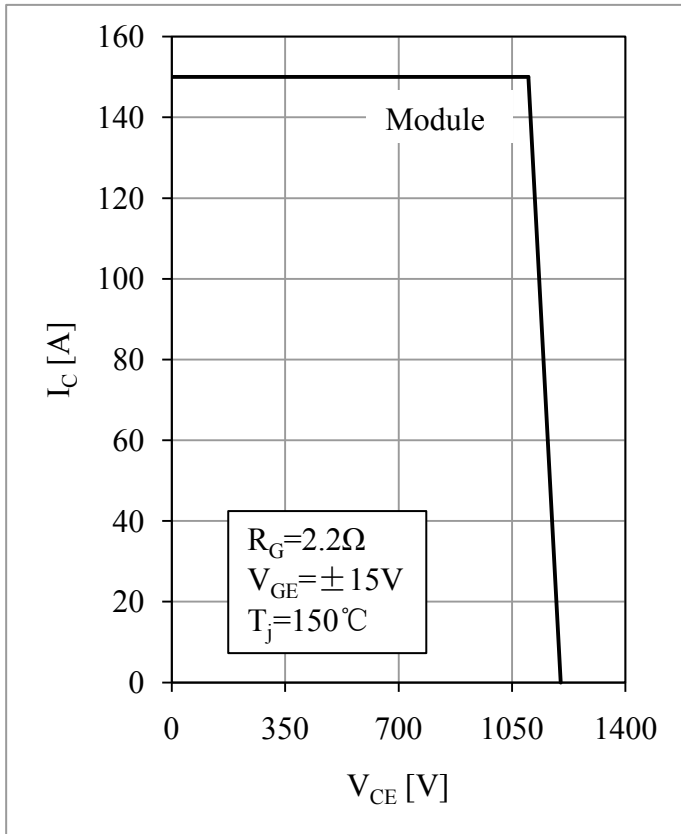


Fig 5. RBSOA

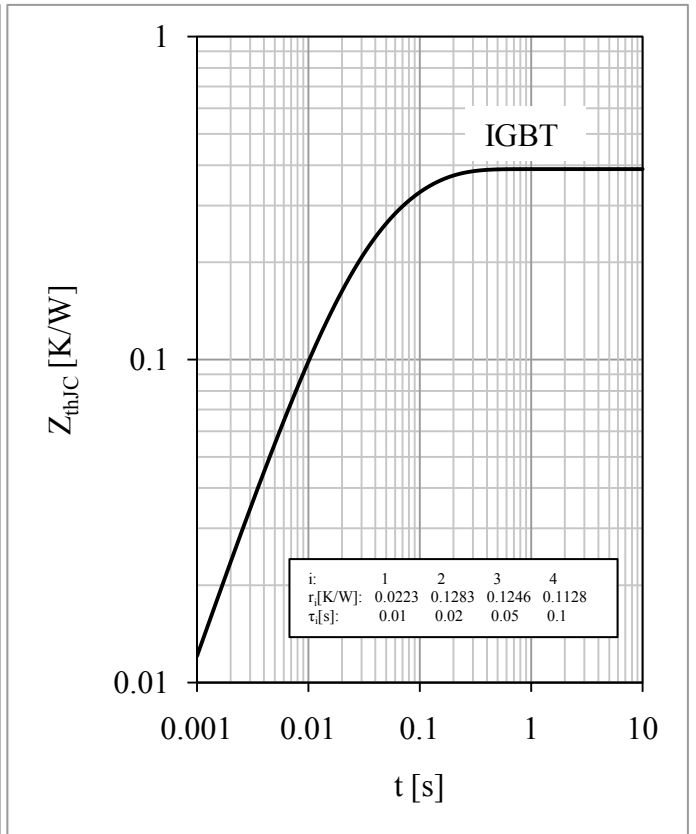


Fig 6. IGBT Transient Thermal Impedance

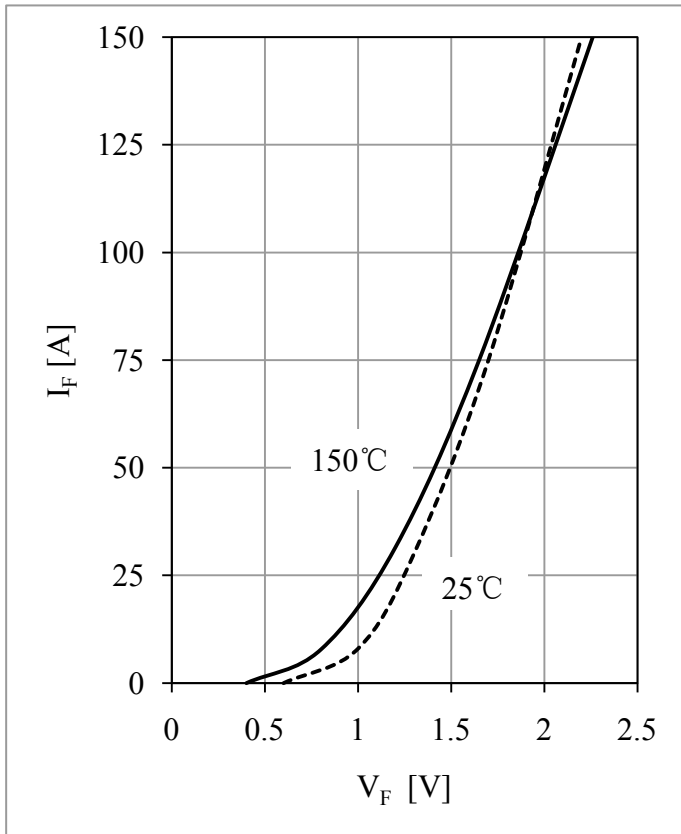


Fig 7. Diode Forward Characteristics

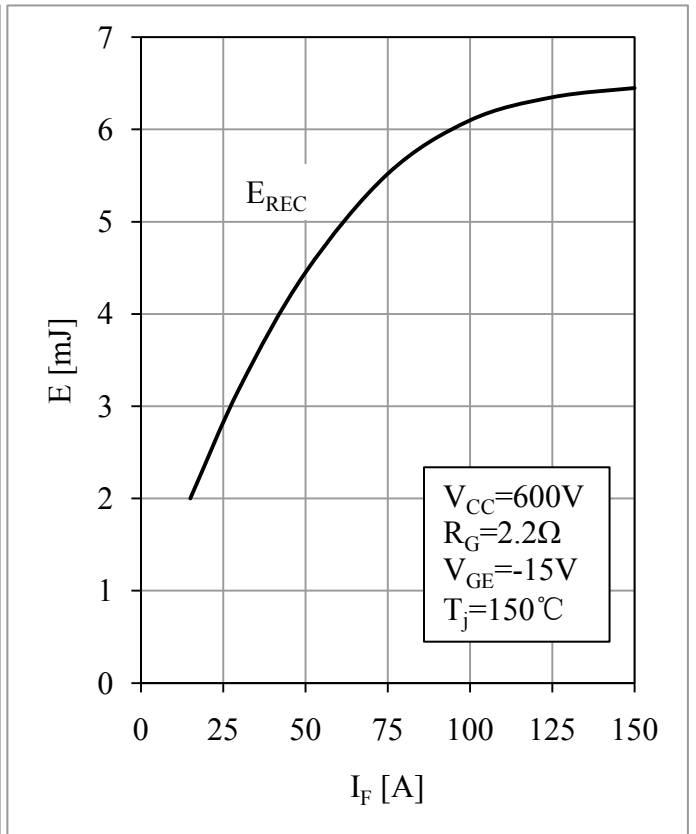


Fig 8. Diode Switching Loss vs. I_F

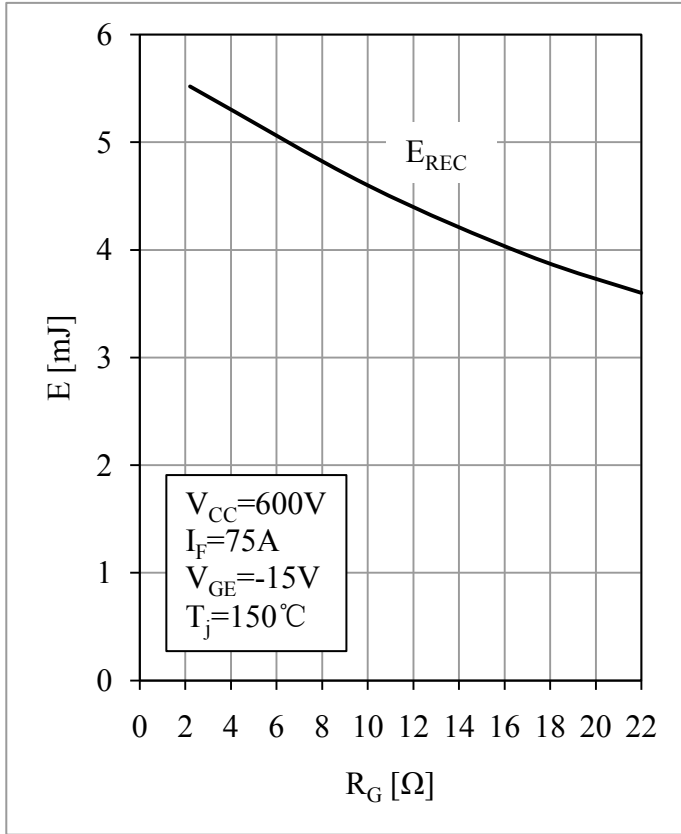


Fig 9. Diode Switching Loss vs. R_G

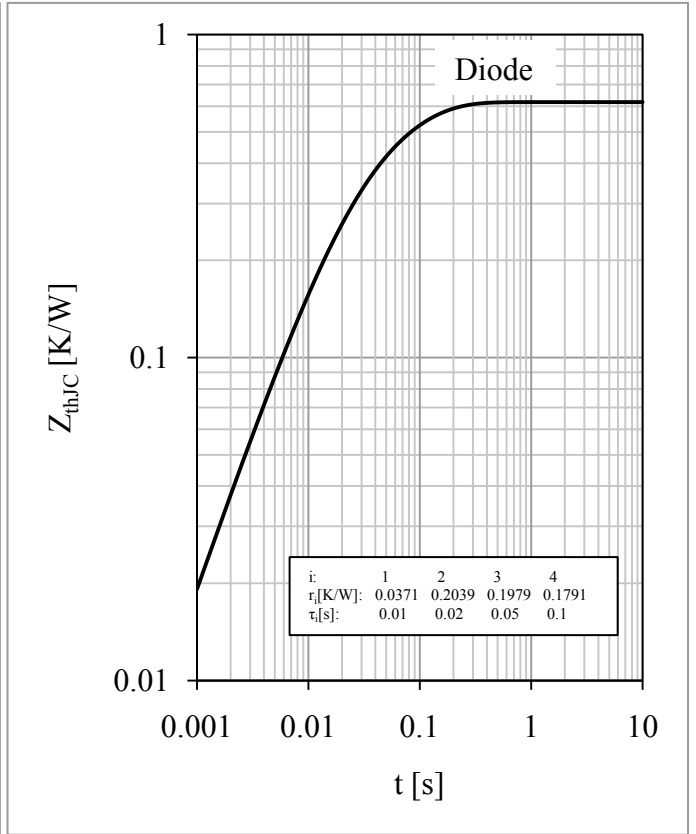
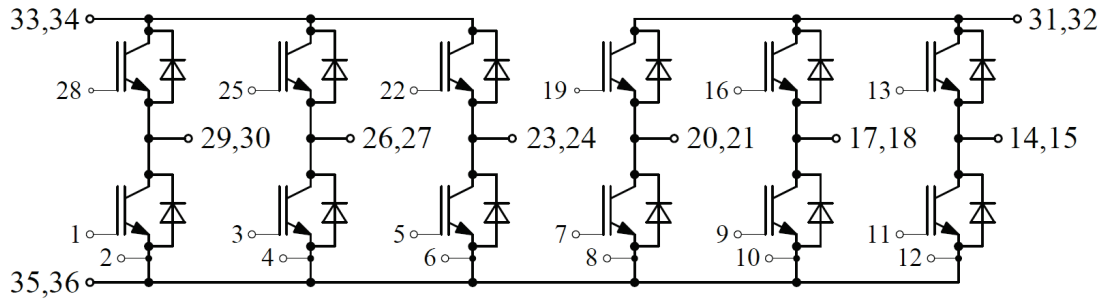


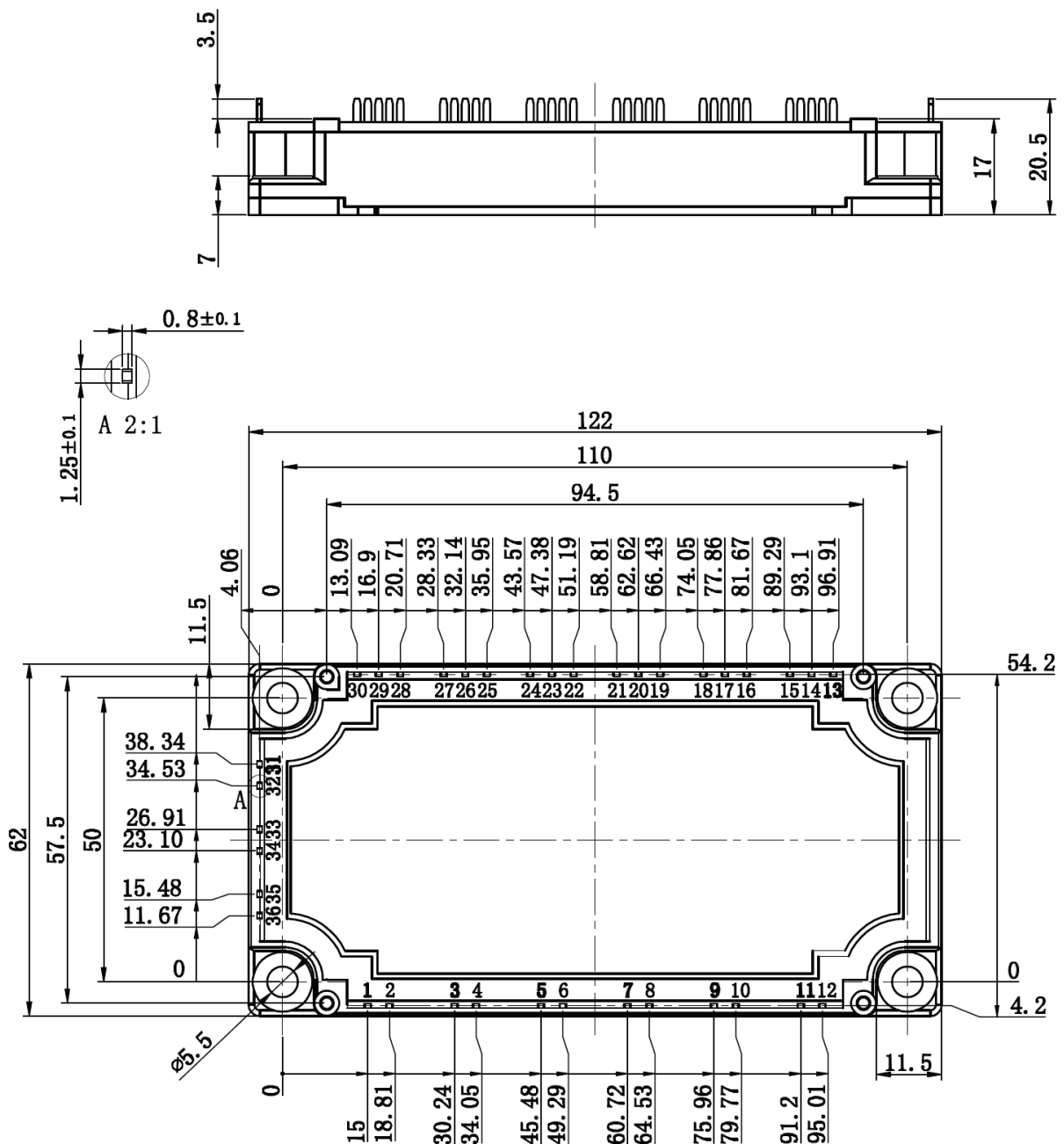
Fig 10. Diode Transient Thermal Impedance

Circuit Schematic



Package Dimensions

Dimensions in Millimeters



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